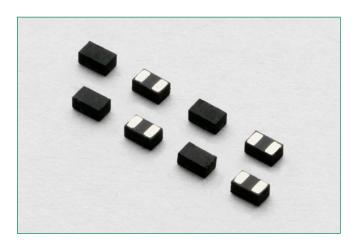
200W Discrete Bidirectional TVS Diode









Additional Information







Accessories



Samples

Description

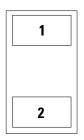
The Bidirectional SPHV-C series is designed for use in portable applications, LED lighting modules, automotive applications, and low speed I/Os. It will protect sensitive equipment from damage due to electrostatic discharge (ESD) and other overvoltage

The SPHV-C series can safely absorb repetitive ESD strikes above the maximum level of the IEC 61000-4-2 international standard (Level 4, ±8kV contact discharge) without performance degradation and safely dissipate up to 8A (SPHV12-C) of induced surge current (IEC 61000-4-5, 2nd Edition tP=8/20µs) with very low clamping voltages.

Features & Benefits

- ESD, IEC 61000-4-2, ±30kV contact, ±30kV air
- EFT, IEC 61000-4-4, 40A (5/50ns)
- Lightning, IEC 61000-4-5 2nd Edition, 8A (tP=8/20µs, SPHV12-C)
- Low clamping voltage
- Low leakage current
- Small SOD882 packaging helps save board space
- AEC-Q101 Qualified
- Halogen free, Lead free and RoHS compliant
- Moisture Sensitivity Level(MSL -1)

Pinout



Applications

- LED Lighting Modules
- Portable Instrumentation
- General Purpose I/O
- Mobile & Handhelds
- RS232 / RS485
- CAN and LIN Bus

Functional Block Diagram



Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.



Absolute Maximum Ratings

Symbol	Parameter	Value	Units
P_{pk}	Peak Pulse Power (t _p =8/20µs)	200	W
T_{OP}	Operating Temperature	-40 to 125	°C
T _{STOR}	Storage Temperature	-55 to 150	°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

SPHV12-C Electrical Characteristics (T_{OP} =25°C)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Reverse Standoff Voltage	V_{RWM}	I _R ≤1μA			12.0	V
Breakdown Voltage	$V_{_{\mathrm{BR}}}$	I _R =1mA	13.3			V
Reverse Leakage Current	I _{LEAK}	V _R =12V			1.0	μΑ
Claran Valtagal	\/	$I_{pp}=1A, t_{p}=8/20 \mu s, Fwd$			19.0	V
Clamp Voltage ¹ V _c	I _{pp} =8A, t _p =8/20μs, Fwd			25.0	V	
Dynamic Resistance ²	R _{DYN}	TLP, $t_p = 100$ ns, I/O to GND		0.48		Ω
Peak Pulse Current	l _{pp}	t _p =8/20μs			8.0	А
		IEC61000-4-2 (Contact Discharge)	±30			kV
ESD Withstand Voltage ¹	V _{ESD}	IEC61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{I/O-I/O}	Reverse Bias=0V, f=1MHz			30	pF

Note:

$\textbf{SPHV15-C Electrical Characteristics} \; (\textbf{T}_{\text{OP}} = 25^{\text{o}} \textbf{C})$

Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Reverse Standoff Voltage	V_{RWM}	I _R ≤1μA			15.0	V
Breakdown Voltage	V _{BR}	I _R =1mA	16.7			V
Reverse Leakage Current	I _{LEAK}	$V_R = 15V$			1.0	μΑ
Clamp Voltage ¹	\/	$I_{pp} = 1A$, $t_{p} = 8/20 \mu s$, Fwd			22.0	V
	V _c	$I_{pp} = 5A$, $t_p = 8/20 \mu s$, Fwd			30.0	V
Dynamic Resistance ²	R _{DYN}	TLP, $t_p = 100$ ns, I/O to GND		0.43		Ω
Peak Pulse Current	l _{pp}	t _p =8/20µs			5.0	А
ECD \\ \(\text{\tint{\text{\tin}\text{\text{\text{\text{\text{\text{\text{\text{\text{\text{\text{\text{\text{\text{\text{\text{\text{\text{\text{\tex{\tex	\/	IEC61000-4-2 (Contact Discharge)	±30			kV
ESD Withstand Voltage ¹	V _{ESD}	IEC61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{I/O-I/O}	Reverse Bias=0V, f=1MHz			24	pF

- 1. Parameter is guaranteed by design and/or device characterization.
 2. Transmission Line Pulse (TLP) with 100ns width and 200ps rise time.



^{1.} Parameter is guaranteed by design and/or device characterization.

^{2.} Transmission Line Pulse (TLP) with 100ns width and 200ps rise time.

200W Discrete Bidirectional TVS Diode

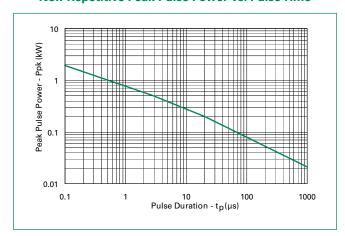
SPHV24-C Electrical Characteristics $(T_{OP}=25^{\circ}C)$

Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Reverse Standoff Voltage	V_{RWM}	I _R ≤1μA			24.0	V
Breakdown Voltage	V_{BR}	I _R =1mA	26.7			V
Reverse Leakage Current	I _{LEAK}	$V_R = 24V$			1.0	μΑ
Clamp Voltage ¹ V _c	\/	$I_{pp} = 1A$, $t_{p} = 8/20 \mu s$, Fwd			36.0	V
	v _C	$I_{pp} = 3A$, $t_{p} = 8/20 \mu s$, Fwd			50.0	V
Dynamic Resistance ²	R _{DYN}	TLP, $t_p = 100$ ns, I/O to GND		0.65		Ω
Peak Pulse Current	l _{pp}	t _p =8/20µs			3.0	А
ESD Withstand Voltage ¹	\/	IEC61000-4-2 (Contact Discharge)	±24			kV
	V _{ESD}	IEC61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{I/O-I/O}	Reverse Bias=0V, f=1MHz			17	pF

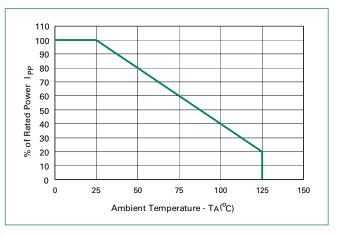
SPHV36-C Electrical Characteristics (T_{OP} =25°C)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Reverse Standoff Voltage	V_{RWM}	I _R ≤1μA			36.0	V
Breakdown Voltage	$V_{_{BR}}$	I _R =1mA	40.0			V
Reverse Leakage Current	I _{LEAK}	V _R =36V			1.0	μΑ
Clamp Voltage ¹	\/	$I_{pp} = 1A$, $t_p = 8/20 \mu s$, Fwd			52.0	V
	V _C	$I_{pp} = 2A$, $t_p = 8/20 \mu s$, Fwd			65.0	V
Dynamic Resistance ²	R_{DYN}	TLP, $t_p = 100$ ns, I/O to GND		1.33		Ω
Peak Pulse Current	l _{pp}	t _p =8/20µs			2.0	А
FCD \\ (\frac{1}{2} \rightarrow \rightarro	\/	IEC61000-4-2 (Contact Discharge)	±15			kV
ESD Withstand Voltage ¹	V _{ESD}	IEC61000-4-2 (Air Discharge)	±20			kV
Diode Capacitance ¹	C _{I/O-I/O}	Reverse Bias=0V, f=1MHz			13	pF

Non-Repetitive Peak Pulse Power vs. Pulse Time



Power Derating Curve





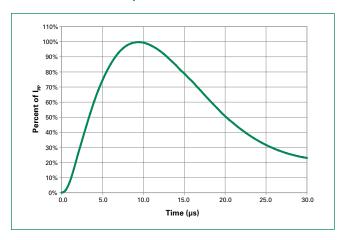
Parameter is guaranteed by design and/or device characterization.
 Transmission Line Pulse (TLP) with 100ns width and 200ps rise time.

Note:
1. Parameter is guaranteed by design and/or device characterization.

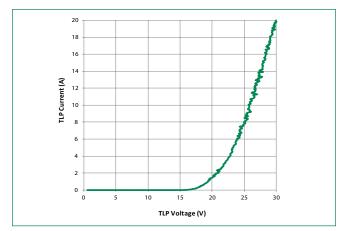
^{2.} Transmission Line Pulse (TLP) with 100ns width and 200ps rise time.

200W Discrete Bidirectional TVS Diode

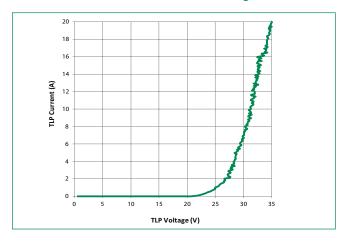
8/20µs Pulse Waveform



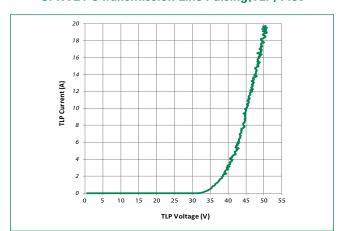
SPHV12-C Transmission Line Pulsing(TLP) Plot



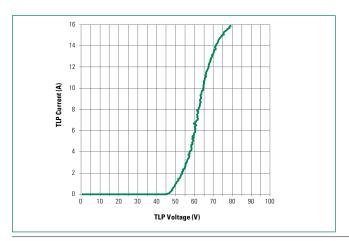
SPHV15-C Transmission Line Pulsing(TLP) Plot



SPHV24-C Transmission Line Pulsing(TLP) Plot



SPHV36-C Transmission Line Pulsing(TLP) Plot

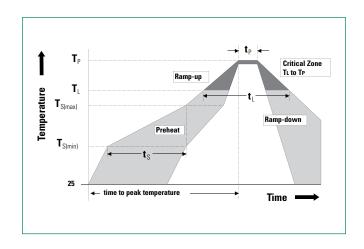




200W Discrete Bidirectional TVS Diode

Soldering Parameters

Reflow Cond	Reflow Condition		
	-Temperature Min (T _{s(min)})	150°C	
Pre Heat	- Temperature Max (T _{s(max)})	200°C	
	-Time (min to max) (t _s)	60 - 120 secs	
Average ram	Average ramp up rate (Liquidus) Temp (T_L) to peak		
$T_{_{S(max)}}$ to $T_{_{L}}$ - Ramp-up Rate		3°C/second max	
Reflow	- Temperature (T _L) (Liquidus)	217°C	
	- Temperature (t _L)	60 – 150 seconds	
Peak Tempera	260 ^{+0/-5} °C		
Time within	5°C of actual peak Temperature (t _p)	30 seconds	
Ramp-down Rate		6°C/second max	
Time 25°C to	8 minutes Max.		
Do not excee	d	260°C	



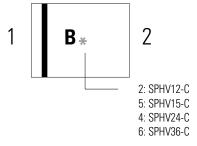
Product Characteristics

Lead Plating	Matte Tin, Pre-Plated Frame
Lead Material	Copper Alloy
Substitute Material	Silicon
Body Material	Molded Compound
Flammability	UL Recoginized compound meeting flammability rating V-0

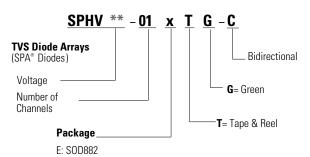
Ordering Information

Part Number	Package	Marking	Min. Order Qty.
SPHV12-01ETG-C		B2	
SPHV15-01ETG-C	SOD882	B5	10000
SPHV24-01ETG-C	300882	B4	10000
SPHV36-01ETG-C		В6	

Part Marking System

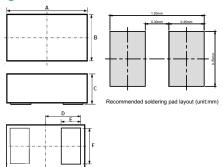


Part Numbering System



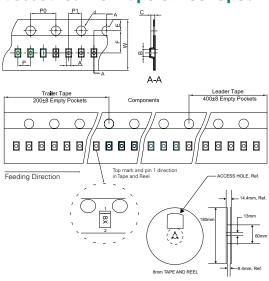


Package Dimensions — SOD882(SPHVxx-01ETG-C)



	Package			SOD882		
Symbol	JEDEC			MO-236		
Syllibol	I	Millimeters	3		Inches	
	Min	Тур	Max	Min	Тур	Max
Α	0.90	1.00	1.10	0.037	0.039	0.041
В	0.50	0.60	0.70	0.022	0.024	0.026
С	0.40	0.50	0.60	0.016	0.020	0.024
D		0.45			0.018	
E	0.20	0.25	0.35	0.008	0.010	0.012
F	0.45	0.50	0.55	0.018	0.020	0.022

Embossed Carrier Tape & Reel Specification



Symbol	Millimeters
Α	0.70+/-0.045
В	1.10+/-0.045
С	0.65+/-0.045
d	1.55+/-0.10
E	1.75+/-0.05
F	3.50+/-0.05
P	2.00+/-0.10
P0	4.00+/-0.10
P1	2.00+/-0.10
W	8.00 + 0.30 -0.10





Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Littelfuse:

SPHV12-01ETG-C SPHV15-01ETG-C SPHV24-01ETG-C SPHV36-01ETG-C SPHV36-01KTG-C SPHV36-01KTG-C SPHV36-01KTG-C